

Silicon Sputtering Target Materials Specifications

Description	Specifications	Note
Materials	High Purity Silicon, Poly or Single Crystal, 5N-8N purity	Dopants other than B are also available
Resistivity	<0.02 Ohmcm	Depends on dopant level
Type	P-type, B doped, or according to customer requirement	
Shape	Planar, circular, rectangular, ring, conical, and custom configuration	Irregular shape available
Dimension	Typical sizes include (mm) 70X27X6; 149.6X70X7; 115X110X4; 100X100X16; 300X100X8; 266X100X14 230X110X4; Ø160X12; Ø150X24	Single crystal up to 300mm
Tolerance	Standard +/-0.1mm, +/-0.05mm	
Parallelism	< 0.05mm	
Perpendicularity	<0.05mm	
Finish	14um fine ground	

Send your enquiries to

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Free test trial samples are available in limited quantities.

Date updated: Mar 29th, 2008
 Specifications could be changed without notice.